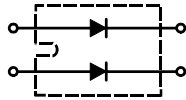
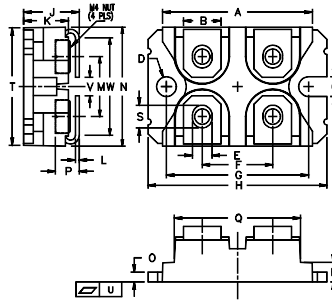


HUR2x100-40

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes



Dimensions SOT-227(ISOTOP)



| Dim. | Millimeter | | Inches | |
|------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 31.50 | 31.88 | 1.240 | 1.255 |
| B | 7.80 | 8.20 | 0.307 | 0.323 |
| C | 4.09 | 4.29 | 0.161 | 0.169 |
| D | 4.09 | 4.29 | 0.161 | 0.169 |
| E | 4.09 | 4.29 | 0.161 | 0.169 |
| F | 14.91 | 15.11 | 0.587 | 0.595 |
| G | 30.12 | 30.30 | 1.186 | 1.193 |
| H | 37.80 | 38.20 | 1.489 | 1.505 |
| J | 11.68 | 12.22 | 0.460 | 0.481 |
| K | 8.92 | 9.60 | 0.351 | 0.378 |
| L | 0.76 | 0.84 | 0.030 | 0.033 |
| M | 12.60 | 12.85 | 0.496 | 0.506 |
| N | 25.15 | 25.42 | 0.990 | 1.001 |
| O | 1.98 | 2.13 | 0.078 | 0.084 |
| P | 4.95 | 5.97 | 0.195 | 0.235 |
| Q | 26.54 | 26.90 | 1.045 | 1.059 |
| R | 3.94 | 4.42 | 0.155 | 0.174 |
| S | 4.72 | 4.85 | 0.186 | 0.191 |
| T | 24.59 | 25.07 | 0.968 | 0.987 |
| U | -0.05 | 0.1 | -0.002 | 0.004 |
| V | 3.30 | 4.57 | 0.130 | 0.180 |
| W | 0.780 | 0.830 | 0.031 | 0.033 |

| | V_{RSM} | V_{RRM} |
|--------------------|-----------|-----------|
| | V | V |
| HUR2x100-40 | 400 | 400 |

| Symbol | Test Conditions | Maximum Ratings | Unit |
|------------------------------------|---|---------------------------------|-------------|
| I_{FRMS} I_{FAVM} | $T_C=60^{\circ}C$; rectangular, $d=0.5$ | 100 | A |
| I_{FSM} | $T_{VJ}=45^{\circ}C$; $t_p=10ms$ (50Hz), sine | 1000 | A |
| E_{AS} | $T_{VJ}=25^{\circ}C$; non-repetitive; $I_{AS}=4A$; $L=182\mu H$ | 2 | mJ |
| I_{AR} | $V_A=1.5 \cdot V_R$ typ.; $f=10kHz$; repetitive | 0.4 | A |
| T_{VJ} T_{VJM} T_{stg} | | -40...+150 150 -40...+150 | $^{\circ}C$ |
| P_{tot} | $T_C=25^{\circ}C$ | 200 | W |
| V_{ISOL} | 50/60Hz, RMS $I_{ISOL} \leq 1mA$ | 2500 | V~ |
| M_d | mounting torque (M4) terminal connection torque (M4) | 1.1-1.5/9-13 1.1-1.5/9-13 | Nm/lb.in. |
| Weight | typical | 30 | g |



HUR2x100-40

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes

| Symbol | Test Conditions | Characteristic Values | | Unit |
|--|---|-----------------------|--------------|------|
| | | typ. | max. | |
| I_R | T _{VJ} =25°C; V _R =V _{RRM} T _{VJ} =150°C; V _R =V _{RRM} | | 1 4 | mA |
| V_F | I _F =100A; T _{VJ} =150°C T _{VJ} =25°C | | 1.24 1.54 | V |
| R_{thJC} R_{thCH} | with heatsink compound | 0.1 | 0.6 | K/W |
| t_{rr} | I _F =1A; -di/dt=400A/us; V _R =30V; T _{VJ} =25°C | 30 | | ns |
| I_{RM} | V _R =100V; I _F =200A; -diF/dt=100A/us; T _{VJ} =100°C | 5.5 | 6.8 | A |

FEATURES

- * International standard package miniBLOC
- * Isolation voltage 2500 V~
- * 2 independent FRED in 1 package
- * Glass passivated chips
- * Very short recovery time
- * Extremely low switching losses
- * Low I_{RM}-values
- * Soft recovery behaviour
- * RoHS compliant

APPLICATIONS

- * Antiparallel diode for high frequency switching devices
- * Antisaturation diode
- * Snubber diode
- * Free wheeling diode in converters and motor control circuits
- * Rectifiers in switch mode power supplies (SMPS)
- * Inductive heating
- * Uninterruptible power supplies (UPS)
- * Ultrasonic cleaners and welders

ADVANTAGES

- * Avalanche voltage rated for reliable operation
- * Soft reverse recovery for low EMI/RFI
- * Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Sirectifier®